## NSN 5961-01-079-6848

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View Online at https://aerobasegroup.com/nsn/5961-01-079-6848 **Inclosure Material:** Metal **Overall Length:** 1.646 inches **Mounting Facility Quantity: Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Overall Width Across Flats:** 0.650 inches Thread Size: 0.250 inches **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 800.0 repetitive peak off-state voltage and 800.0 repetitive peak reverse voltage and 960.0 nonrepetitive peak reverse voltage **Current Rating Per Characteristic:** 300.00 amperes peak forward surge current nanoamperes and 22.00 amperes forward current, total rms universal **Power Rating Per Characteristic:** 60.0 watts small-signal input power, common-collector blank and 0.5 watts small-signal input power, common-collector universal **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius case **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud **Specification Data:** 80131-release 5830 manufacturers specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0